PATENT NO. : 7,101,795 B1 Page 1 of 5

APPLICATION NO.: 09/678266
DATED: September 5, 2006

INVENTOR(S) : Xi et al.

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Title Page, Item (63), Related U.S. Application Data: Please add the following priority data:

--Continuation-in-part of application No. 09/605,593, filed on Jun. 28, 2000, now Pat. No. 6,551,929.--

Title Page, Item (56), References Cited, U.S. PATENT DOCUMENTS: Please include the following references:

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DATED : September 5, 2006

INVENTOR(S) : Xi et al.

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

#### Title Page, Item (56), (cont'd)

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APPLICATION NO.: 09/678266

DATED

: September 5, 2006

INVENTOR(S)

: Xi et al.

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Title Page, Item (56), References Cited, FOREIGN PATENT DOCUMENTS: Please include the following references:

WO 01/29893	4/2001
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WO 02/45167	6/2002
WO 02/067319	8/2002
WO 01/66832	9/2001
EP 1167569	1/2002

Title Page, Item (56), References Cited, OTHER PUBLICATIONS: Please include the following references:

--Klaus, et al. "Atomically Controlled Growth of Tungsten and Tungsten Nitride Using Sequential Surface Reactions," Applied Surface Science, 162-163 (2000) 479-491.

"Pulsed Nucleation for Ultra-High Aspect Ratio Tungsten Plugfill"; San-Hyeob Lee et al.; Materials Research Society, 2002, 649-653.

Yang et al. "Atomic Layer Deposition of Tungsten Film from WF<sub>6</sub>/B<sub>2</sub>H<sub>6</sub>: Nucleation Layer for Advanced Semiconductor Device," Conference Proceedings ULSI XVII (2002) Materials Research Society.--

Column 1, Line 6: Before Background of the Disclosure, insert

-- This application is a continuation-in-part of U.S. Patent Application Serial No. 09/605,593, filed June 28, 2000, now issued as U.S. Patent No. 6,551,929.--

Column 5, Line 13: Change "Aax" to -- Aax--

Column 5, Line 22: Change "to" to --t<sub>1</sub>--

Column 7, Claim 1, Line 34: Before "layer", insert --nucleation layer and a bulk deposition--

Column 7, Claim 1, Line 36: Before "nucleation", insert --refractory metal--

Column 7, Claim 1, Line 38: Delete "atop of said nucleation layer,"

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APPLICATION NO.: 09/678266
DATED: September 5, 2006

INVENTOR(S) : Xi et al.

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Column 7, Claim 1, Line 39: Before "employing", insert --on said nucleation layer by--

Column 7, Claim 1, Line 40: Change "subject said nucleation layer to a bulk deposition of a compound" to --bulk deposit refractory metal--

Column 7, Claim 2, Line 43: Delete "forming atop of said nucleation layer includes forming"

Column 7, Claim 2, Line 45: Before "employing", insert -- is deposited--

Column 7, Claim 3, Line 46: Delete "forming atop of said nucleation layer includes forming"

Column 7, Claim 3, Line 48: Before "employing", insert -- is deposited--

Column 7, Claim 4, Line 50: Delete "introducing said first and second gases therein so as to purge said processing chamber of said first reactive gas by"

Column 8, Claim 4, Line 1: Change "therein," to --into the processing chamber after exposing said substrate to the first reactive gas and--

Column 8, Claim 6, Line 9: Change "a" to --the refractory metal--

Column 8, Claim 6, Line 10: Before "subsequently", insert -- and--

Column 8, Claim 7, Line 15: Change "a" to --the refractory metal--

Column 8, Claim 9, Line 22: Change "subject" to --subjecting--

Column 8, Claim 10, Line 24: Before "layer", insert --nucleation layer and a bulk deposition--

Column 8, Claim 10, Line 27: Before "while", insert --wherein said second reactive gas comprises a refractory metal selected from the group consisting of titanium (Ti) and tungsten (W),--

Column 8, Claim 11, Line 38: Delete "said second reactive gas includes a refractory metal and"

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DATED : September 5, 2006 INVENTOR(S) : Xi et al.

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Column 8, Claim 11, Line 40: Change "includes" to --comprises--

Column 8, Claim 12, Line 42: Delete "selected from the group consisting of titanium (Ti) and"

Column 8, Claim 13, Line 46: Delete "first"

This certificate supersedes Certificate of Correction issued February 13, 2007.

Signed and Sealed this

Sixth Day of March, 2007

JON W. DUDAS
Director of the United States Patent and Trademark Office